

N-Channel Enhancement Mode MOSFET

1. Product Information

1.1 Features

- ☒ Surface-mounted package
- ☒ Advanced trench cell design

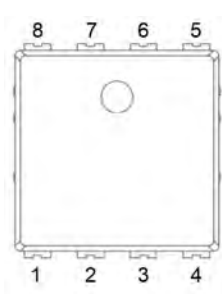
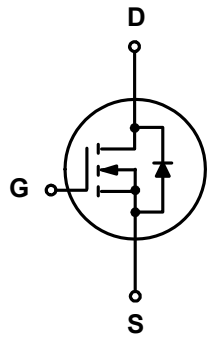
1.2 Applications

- ☒ LCD TV appliances
- ☒ LCDM appliances
- ☒ High power inverter system

1.3 Quick reference

- ☒ $BV \geq 40\text{ V}$
- ☒ $P_{tot} \leq 250\text{ W}$
- ☒ $I_D \leq 300\text{ A}$
- ☒ $R_{DS(ON)} \leq 0.7\text{ m}\Omega @ V_{GS} = 10\text{ V}$
- ☒ $R_{DS(ON)} \leq 1.5\text{ m}\Omega @ V_{GS} = 6\text{ V}$

2. Pin Description

Pin	Description	Simplified Outline	Symbol
1	Gate(G)	 Top View PDFN 8x8-8L	
2,3,4	Source(S)		
5,6,7,8	Drain(D)		

3. Limiting Values

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	Drain-Source Voltage	T _C = 25 °C	-	40	V
V _{GS}	Gate-Source Voltage	T _C = 25 °C	-	±20	V
I _D ^{*,***}	Drain Current (DC)	T _C = 25 °C, V _{GS} = 10 V	-	300	A
		T _C = 100 °C, V _{GS} = 10 V	-	283	A
I _{DM} [*]	Drain Current (Pulsed)	T _C = 25 °C, V _{GS} = 10 V	-	1200	A
P _{tot}	Drain power dissipation	T _C = 25 °C	-	250	W
T _{stg}	Storage Temperature		-55	150	°C
T _J	Junction Temperature		-	150	°C
I _S	Continuous-Source Current	T _C = 25 °C	-	300	A
E _{AS}	Single Pulsed Avalanche Energy	V _{DD} =40V , L=1.0mH	-	2112	mJ
R _{θJA} ^{**}	Thermal Resistance- Junction to Ambient		-	44	°C/W
R _{θJC} ^{**}	Thermal Resistance- Junction to Case		-	0.5	

Notes :

* Pulse width ≤ 300 μs, duty cycle ≤ 2 %

** Surface Mounted on 1 in² pad area, t ≤ 10 sec.

*** Limited by bonding wire

4. Marking Information

Product Name	Marking
UD005N04WH	005N04H YWW01 AAAAAA YWW01: Date Code

5. Ordering Code

Product Name	Package	Reel Size	Tape width	Quantity	Note
UD005N04WH	PDFN8*8			2000	

6. Electrical Characteristics (T_A = 25 °C Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _{DS} = 250 μA	40	-	-	V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _{DS} = 250 μA	2	-	4	V
I _{DSS}	Drain Leakage Current	V _{DS} = 32 V, V _{GS} = 0 V	-	-	1	μA
I _{GSS}	Gate Leakage Current	V _{GS} = 0 V, V _{GS} = ± 20 V	-	-	±100	nA
R _{DS(ON)} ^a	On-State Resistance	V _{GS} = 10 V, I _{DS} = 50 A	-	0.6	0.7	m Ω
		V _{GS} = 6 V, I _{DS} = 30 A	-	1.2	1.5	
Diode Characteristics						
V _{SD} ^a	Diode Forward Voltage	I _{SD} = 50 A, V _{GS} = 0 V	-	-	1.3	V
t _{rr}	Reverse Recovery Time	I _{DS} = 50 A, V _{GS} = 0 V dI _{SD} /dt = 100 A/μs	-	39	-	nS
Q _{rr}	Reverse Recovery Charge		-	40	-	nC
Dynamic Characteristics ^b						
C _{iss}	Input Capacitance	V _{GS} = 0 V, V _{DS} = 20 V Frequency = 1 MHz	-	7322	-	pF
C _{oss}	Output Capacitance		-	2935	-	
C _{rss}	Reverse Transfer Capacitance		-	141	-	
t _{d(on)}	Turn-on Delay Time	V _{DS} = 20 V, V _{GEN} = 10 V, R _G = 3.9 Ω, R _L = 0.4 Ω, I _{DS} = 50 A	-	25	-	nS
t _r	Turn-on Rise Time		-	113	-	
t _{d(off)}	Turn-off Delay Time		-	89	-	
t _f	Turn-off Fall Time		-	91	-	
Gate Charge Characteristics ^b						
Q _g	Total Gate Charge	V _{DS} = 20 V, V _{GS} = 10 V, I _{DS} = 50 A	-	123	-	nC
Q _{gs}	Gate-Source Charge		-	39	-	
Q _{gd}	Gate-Drain Charge		-	30	-	

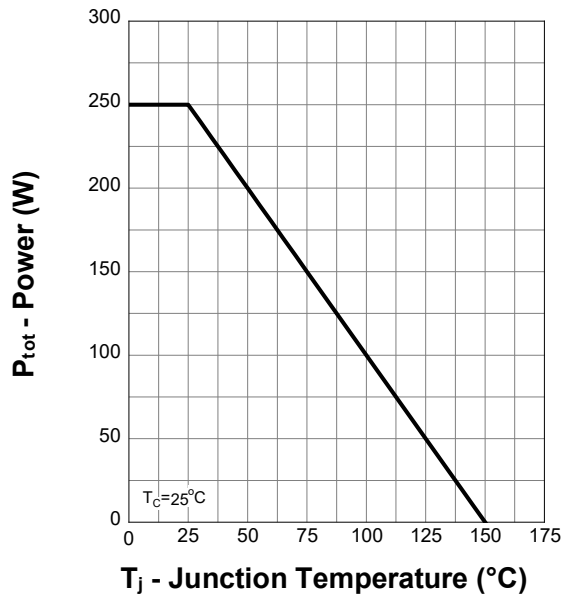
Notes :

a : Pulse test ; pulse width ≤ 300 μs, duty cycle ≤ 2%

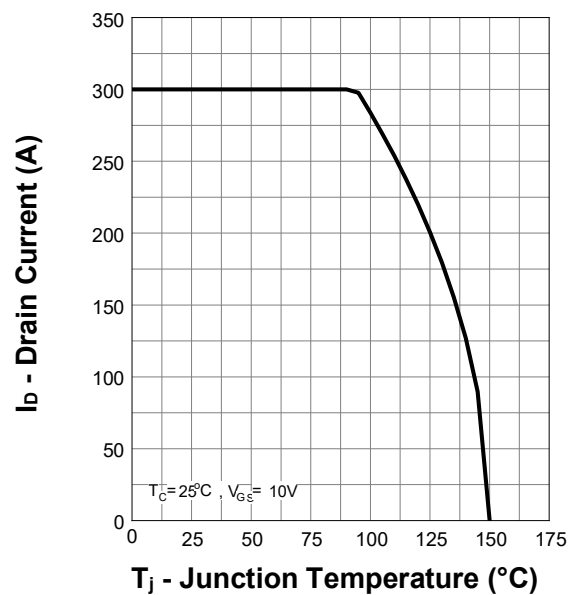
b : Guaranteed by design, not subject to production testing

7. Typical Characteristics

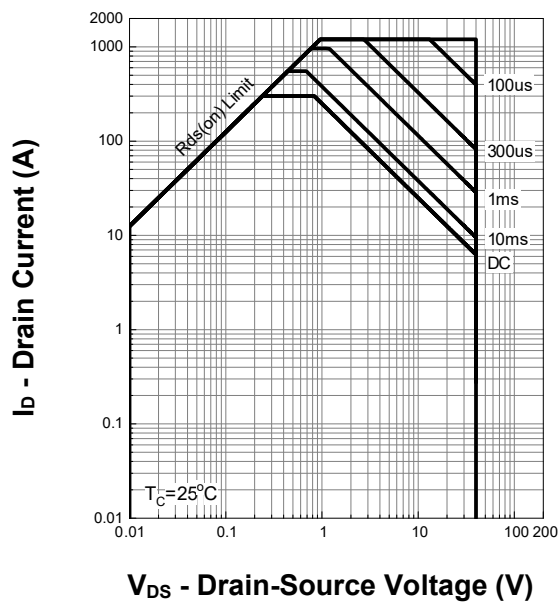
Power Capability



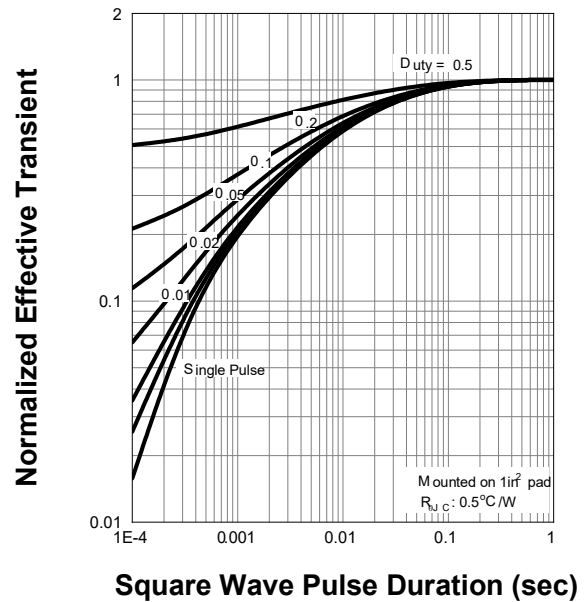
Current Capability



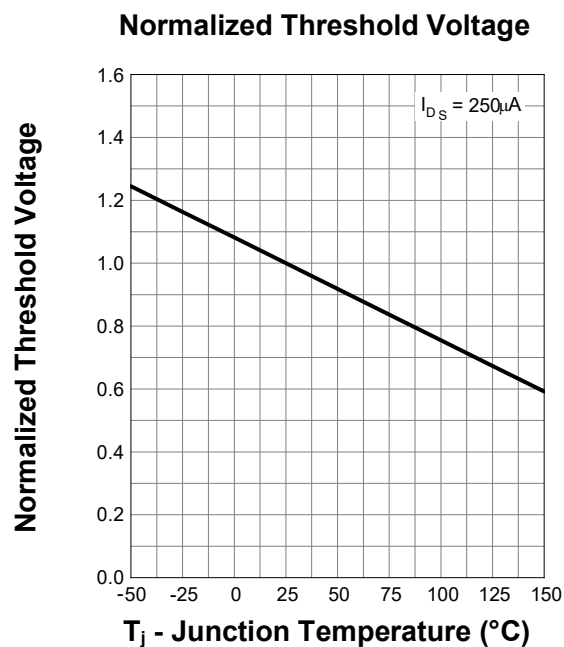
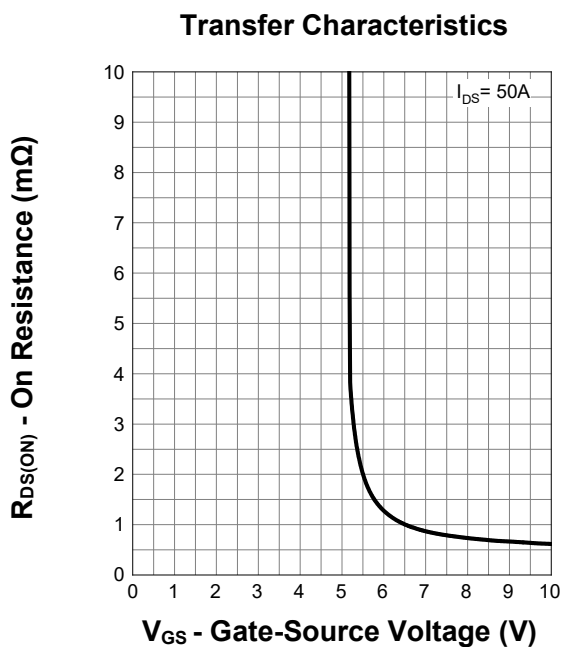
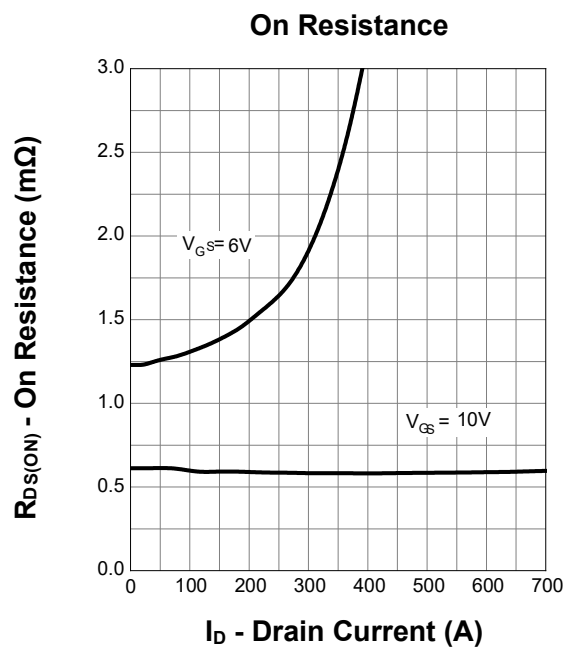
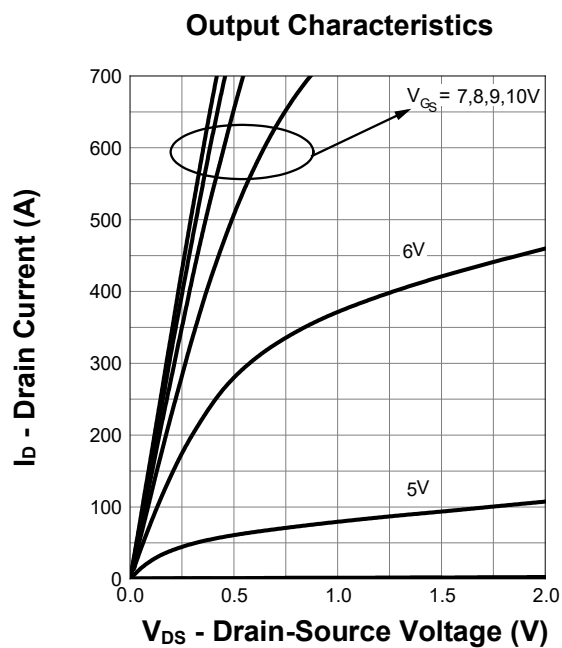
Safe Operating Area



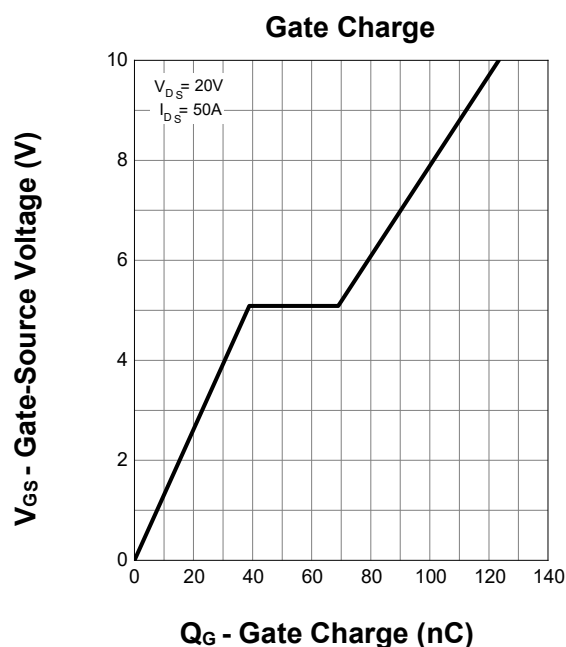
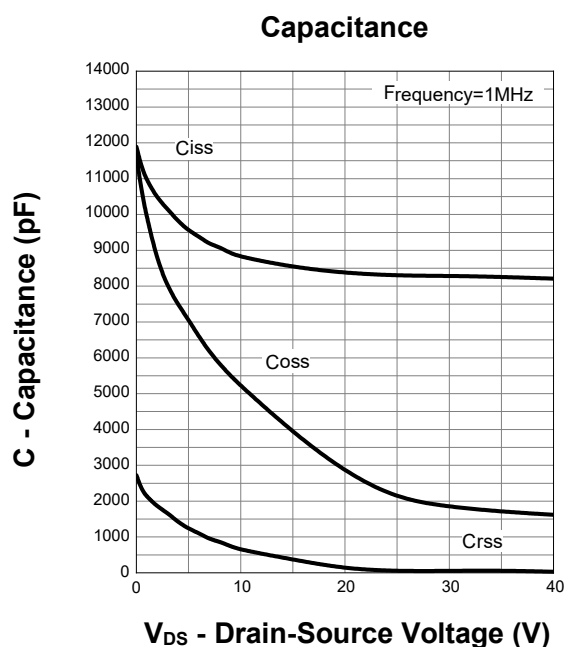
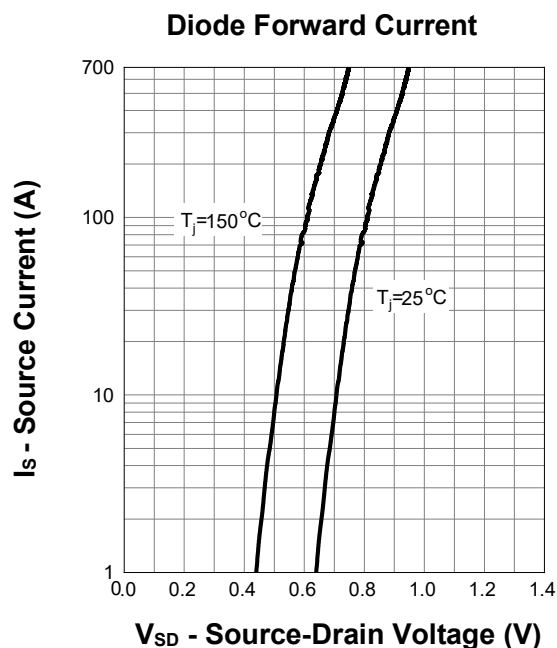
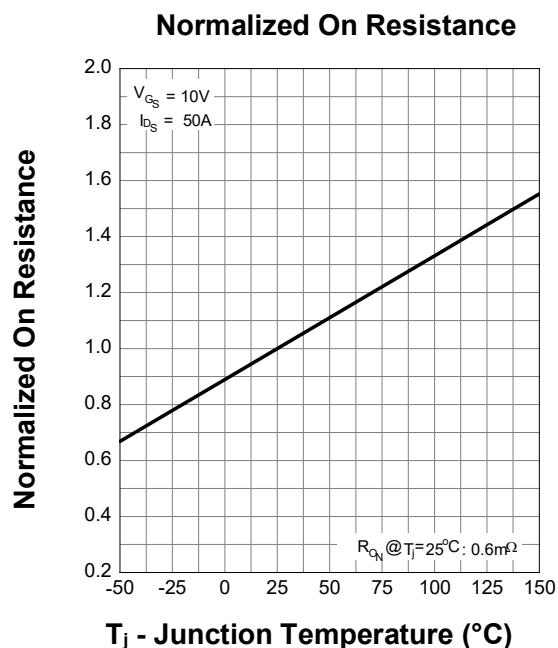
Transient Thermal Impedance



7. Typical Characteristics (cont.)

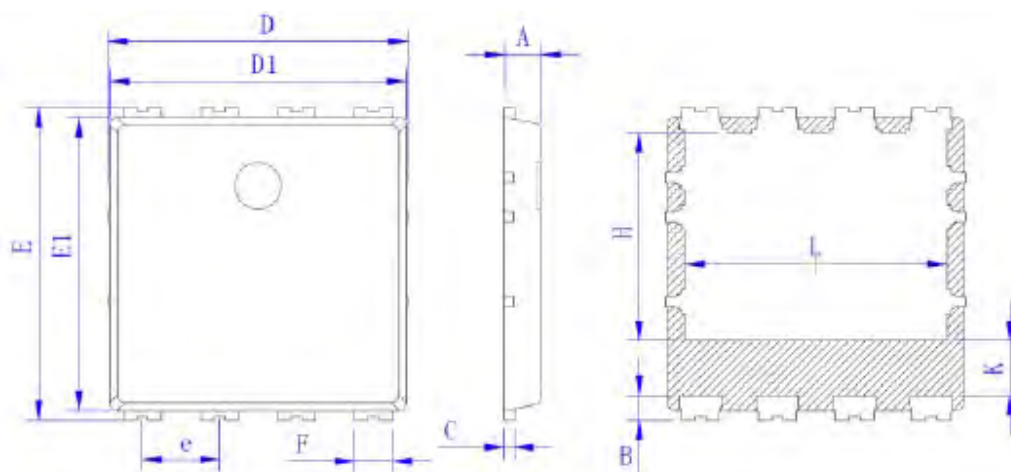


7. Typical Characteristics (cont.)



8. Package Dimensions

PDFN 8x8-8L



Symbol	Dimensions In Millimeters	
	MIN.	MAX.
A	0.9	1.00
B	0.5	0.70
C	0.254 (Typ.)	
D	7.70	7.90
D1	7.60	7.80
E	7.90	8.10
E1	7.40	7.60
e	2.0 (Typ.)	
F	1.00 (Typ.)	
H	5.15	5.40
L	6.60	6.9
K	1.2	-